

Low Leakage Diode

1N3595

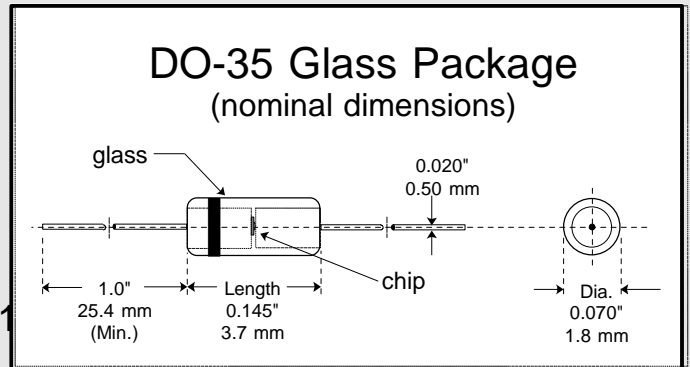
DO-35 Glass Package

Applications

Used in instrumentation applications, where low leakage and high voltage isolation are important.

Features

- Six sigma quality
- Metallurgically bonded
- BKC's Sigma Bond™ plating for problem free solderability
- LL-34/35 MELF SMD available
- Full approval to Mil-S-19500/241
- Available up to JANTXV-1 levels
- "S" level screening available to Source Control Drawings using a DO-35 tungsten, hard glass voidless package for Space applications



Maximum Ratings	Symbol	Value	Unit	
Peak Inverse Voltage	PIV	150 (Min.)	Volts	
Average Rectified Current	I_{Avg}	150	mAmps	
Continuous Forward Current	I_{Fdc}	150	mAmps	
Peak Surge Current ($t_{peak} = 1 \mu\text{sec.}$)	I_{peak}	4.0	Amps	
BKC Power Dissipation @ $T_L = 50^\circ\text{C}$, $L = 3/8"$ from body	P_{tot}	500	mWatts	
Storage & Operating Temperature Range	$T_{St \& Op}$	-65 to +200	$^\circ\text{C}$	
Electrical Characteristics @ 25°C	Symbol	Minimum	Maximum	Unit
Forward Voltage Drop @ $I_F = 1 \text{ mA}$	V_F	0.52	0.68	Volts
Forward Voltage Drop @ $I_F = 5 \text{ mA}$	V_F	0.60	0.75	Volts
Forward Voltage Drop @ $I_F = 10 \text{ mA}$	V_F	0.65	0.80	Volts
Forward Voltage Drop @ $I_F = 50 \text{ mA}$	V_F	0.74	0.88	Volts
Forward Voltage Drop @ $I_F = 100 \text{ mA}$	V_F	0.79	0.92	Volts
Forward Voltage Drop @ $I_F = 200 \text{ mA}$	V_F	0.83	1.0	Volts
Reverse Leakage Current @ $V_R = 125 \text{ V}$	I_R		1.0	nA
Reverse Leakage Current @ $V_R = 125 \text{ V}$	I_R		500 @ 150°C	nA
Capacitance @ $V_R = 0 \text{ V}$, $f = 1 \text{ MHz}$	C_T		8.0	pF
Reverse Recovery Time (note 1)	t_{rr}		3.0	μSecs

Note 1: Per Method 4031-B of MIL-STD-750 with $I_F = 10 \text{ mA}$, $V_R = 35 \text{ V}$, $R_L = 1.0 \text{ K Ohms}$, $C = 10 \text{ Pf}$

For military parts use the 1N3595-1 number with the appropriate JAN, JTX or JTXV prefix.
The SMD DO-213AA comes in commercial (LL3595) and military versions (1N3595UR-1).